

SEMICONDUCTOR IM

FDN339AN N-Channel 2.5V Specified PowerTrench[®] MOSFET

General Description

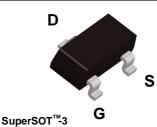
This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

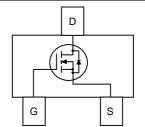
Applications

- DC/DC converter
- Load switch

Features

- 3 A, 20 V. $R_{DS(ON)} = 0.035 \ \Omega \ @ V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 0.050 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Low gate charge (7nC typical).
- High performance trench technology for extremely low $\rm R_{\rm DS(ON)}.$
- High power and current handling capability.





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Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	3	A
	- Pulsed		20	
PD	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C
Therma	I Characteristics			

Package Outlines and Ordering Information

Thermal Resistance, Junction-to-Case

- actuage examines and endering intermation				
Device Marking	Device	Reel Size	Tape Width	Quantity
339	FDN339AN	7"	8mm	3000 units

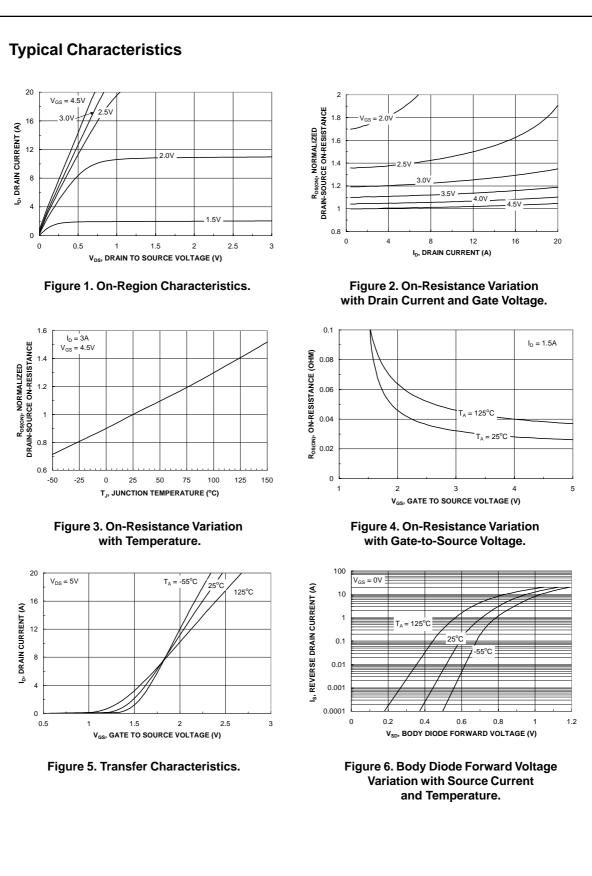
(Note 1)

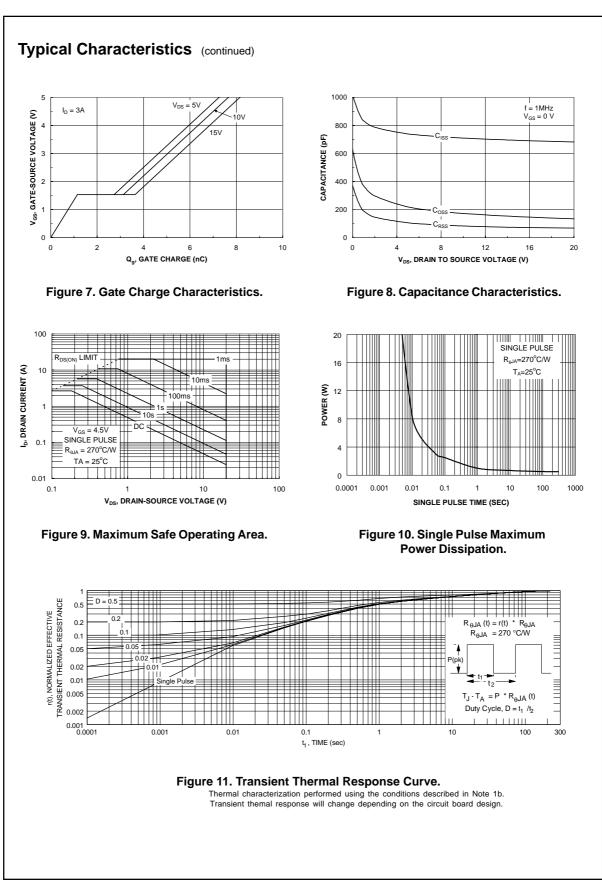
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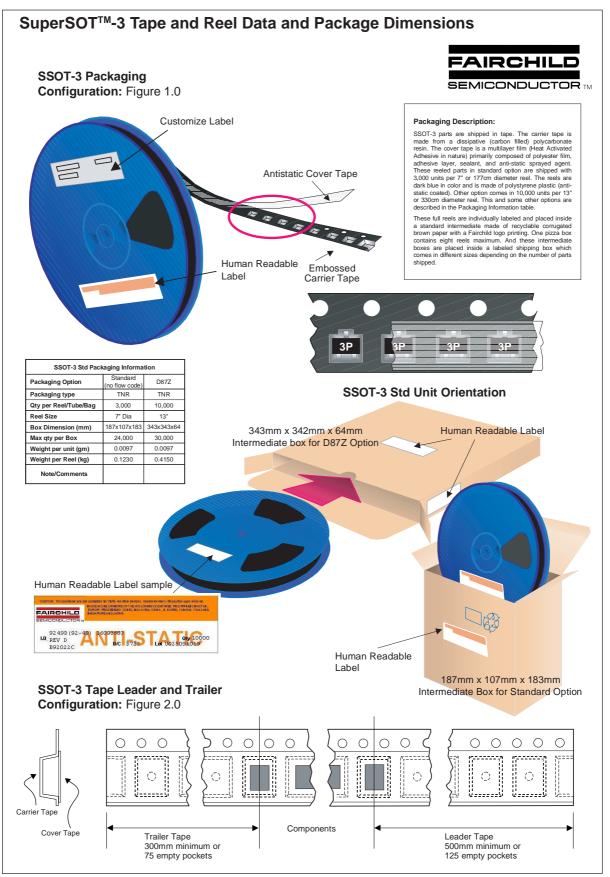
 $R_{\theta JC}$

°C/W

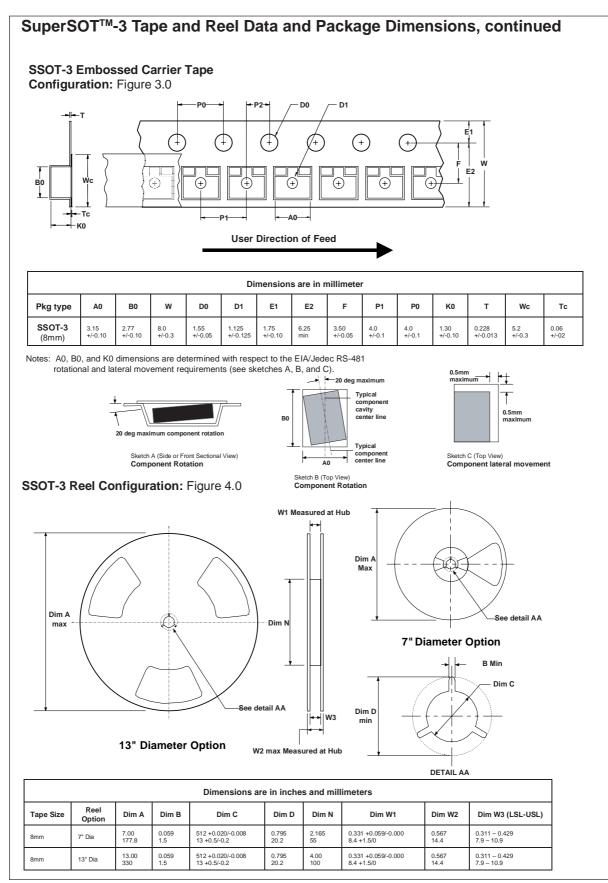
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	20			V
<u>ΔBV_{DSS}</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A,Referenced to 25° C		14		mV/°C
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 16 V, V_{GS} = 0 V$			1	μA
Igssf	Gate-Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.4	0.85	1.5	V
<u>ΔVGS(th)</u> ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$ \begin{array}{c} V_{GS} = 4.5 \ V, \ I_D = 3 \ A \\ V_{GS} = 4.5 \ V, \ I_D = 3 \ A, \ T_J \! = \! 125^\circ \! C \\ V_{GS} = 2.5 \ V, \ I_D = 2.4 \ A \end{array} $		0.029 0.040 0.039	0.035 0.061 0.050	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	10			A
g fs	Forward Transconductance	V _{DS} = 5 V, I _D = 3 A		11		S
Dynamic	Characteristics	-				
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$		700		pF
Coss	Output Capacitance	f = 1.0 MHz		175		pF
Crss	Reverse Transfer Capacitance	-		85		pF
				00		p.
	G Characteristics (Note 2) Turn-On Delay Time	V _{DD} = 10 V, I _D = 1 A,		8	16	ns
d(on)	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		10	18	ns
	Turn-Off Delay Time	_		18	29	
d(off)	Turn-Off Fall Time	_		5	10	ns
i _f Q _g		$\frac{1}{10000000000000000000000000000000000$		5 7	10	ns nC
	Total Gate Charge Gate-Source Charge	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		1.2	10	nC
Q _{gs}	° °	-		1.2		
	Gate-Drain Charge			1.9		nC
	Durce Diode Characteristics a Maximum Continuous Drain-Source		1		0.42	Δ
V _{SD}	Drain-Source Diode Forward Voltage			0.65	1.2	A V
Notes:	sum of the junction-to-case and case-to-ambien	2)				-
Scale 1 :	e drain pins. $R_{_{\theta,JC}}$ is guaranteed by design while $R_{_{\theta CA}}$ is					

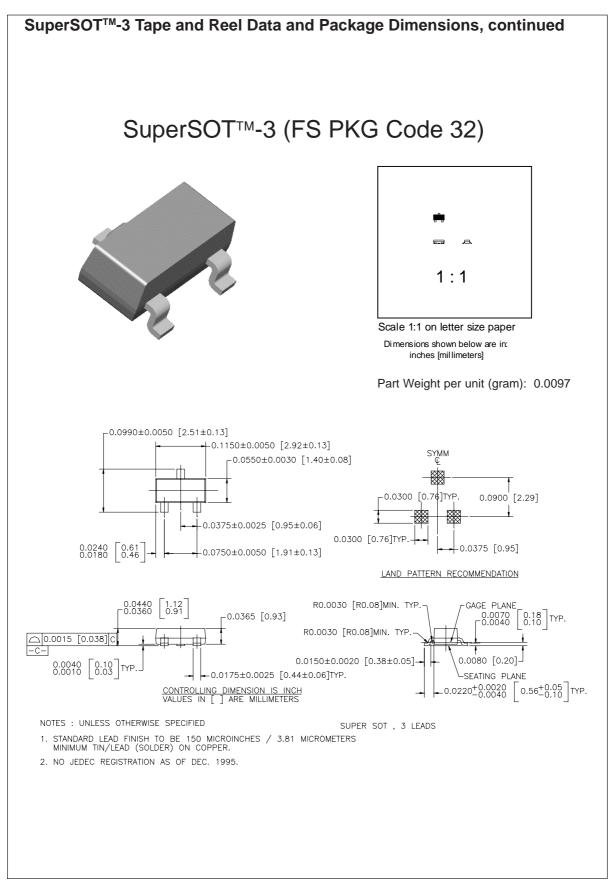






August 1999, Rev. C





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